High Voltage Transistor Surface Mount

NPN Silicon

Features

- PZTA42T1G is Complement to PZTA92T1G
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage (Open Base)	V _{CEO}	300	Vdc
Collector-Base Voltage (Open Emitter)	V _{CBO}	300	Vdc
Emitter-Base Voltage (Open Collector)	V _{EBO}	6.0	Vdc
Collector Current (DC)	I _C	500	mAdc
Total Power Dissipation @ T _A = 25°C (Note 1)	P _D	1.5	W
Storage Temperature Range	T _{stg}	-65 to +150	°C
Junction Temperature	TJ	150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Device mounted on a FR-4 glass epoxy printed circuit board 1.575 in x 1.575 in x 0.0625 in; mounting pad for the collector lead = 0.93 sq in.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	83.3	°C/W

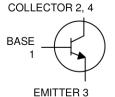
Device mounted on a FR-4 glass epoxy printed circuit board
 1.575 in x 1.575 in x 0.0625 in; mounting pad for the collector lead = 0.93 sq in.



ON Semiconductor®

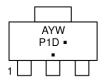
http://onsemi.com

SOT-223 PACKAGE NPN SILICON HIGH VOLTAGE TRANSISTOR SURFACE MOUNT





STYLE 1
MARKING DIAGRAM



P1D = Specific Device Code A = Assembly Location

Y = Year W = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device		Package	Shipping [†]
PZTA42T10	à	SOT-223 (Pb-Free)	1,000 / Tape & Reel
SPZTA42T1	G	SOT-223 (Pb-Free)	1,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_A = 25^{\circ}C \ unless \ otherwise \ noted)$

Characteristics	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	'	•		'
Collector-Emitter Breakdown Voltage (Note 3) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	300	-	Vdc
Collector-Base Breakdown Voltage $(I_C = 100 \mu Adc, I_E = 0)$	V _(BR) CBO	300	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100 \mu Adc, I_C = 0$)	V _{(BR)EBO}	6.0	-	Vdc
Collector-Base Cutoff Current (V _{CB} = 200 Vdc, I _E = 0)	I _{CBO}	-	0.1	μAdc
Emitter-Base Cutoff Current $(V_{BE} = 6.0 \text{ Vdc}, I_C = 0)$	I _{EBO}	-	0.1	μAdc
ON CHARACTERISTICS	•			
DC Current Gain	h _{FE}	25 40 40	- - -	-
DYNAMIC CHARACTERISTICS	•	•	•	•
Current-Gain – Bandwidth Product (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	50	-	MHz
Feedback Capacitance (V _{CB} = 20 Vdc, I _E = 0, f = 1.0 MHz)	C _{re}	-	3.0	pF
Collector-Emitter Saturation Voltage (I _C = 20 mAdc, I _B = 2.0 mAdc)	V _{CE(sat)}	-	0.5	Vdc
Base-Emitter Saturation Voltage (I _C = 20 mAdc, I _B = 2.0 mAdc)	V _{BE(sat)}	-	0.9	Vdc

^{3.} Pulse Test Conditions, t_p = 300 μ s, δ 0.02.

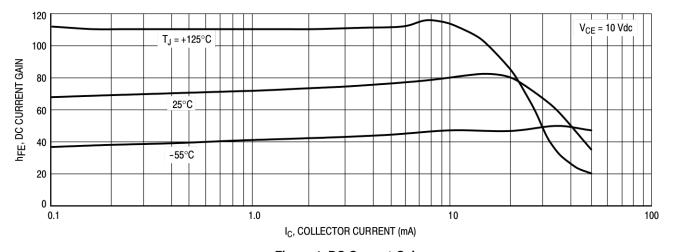


Figure 1. DC Current Gain

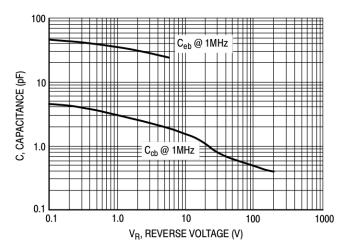
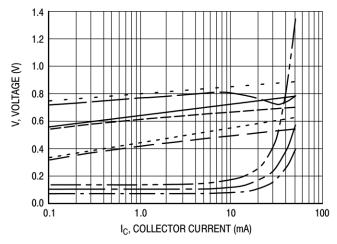
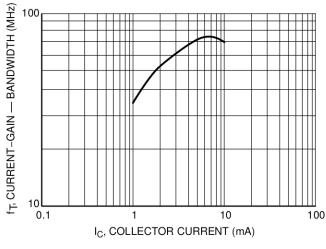


Figure 2. Capacitance



V_{CE(sat)} @ 25°C, I_C/I_B = 10
V_{CE(sat)} @ 125°C, I_C/I_B = 10
V_{CE(sat)} @ -55°C, I_C/I_B = 10
V_{DE(sat)} @ -55°C, I_C/I_B = 10
V_{DE(sat)} @ 25°C, I_C/I_B = 10
V_{DE(sat)} @ 25°C, I_C/I_B = 10
V_{DE(sat)} @ -55°C, I_C/I_B = 10
V_{DE(sat)} @ -55°C, I_C/I_B = 10
V_{DE(sat)} @ 25°C, V_{CE} = 10 V
V_{DE(sat)} @ 25°C, V_{CE} = 10 V
V_{DE(sat)} @ -55°C, V_{CE} = 10 V

Figure 3. "ON" Voltages



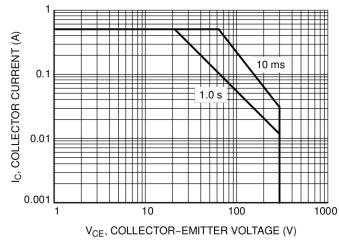
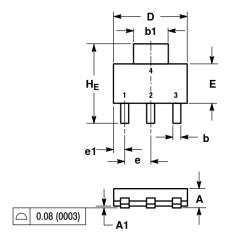


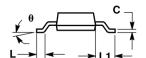
Figure 4. Current Gain Bandwidth Product

Figure 5. Safe Operating Area

PACKAGE DIMENSIONS

SOT-223 (TO-261) CASE 318E-04 ISSUE N





NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	1.50	1.63	1.75	0.060	0.064	0.068	
A1	0.02	0.06	0.10	0.001	0.002	0.004	
b	0.60	0.75	0.89	0.024	0.030	0.035	
b1	2.90	3.06	3.20	0.115	0.121	0.126	
С	0.24	0.29	0.35	0.009	0.012	0.014	
D	6.30	6.50	6.70	0.249	0.256	0.263	
E	3.30	3.50	3.70	0.130	0.138	0.145	
е	2.20	2.30	2.40	0.087	0.091	0.094	
e1	0.85	0.94	1.05	0.033	0.037	0.041	
L	0.20			0.008			
L1	1.50	1.75	2.00	0.060	0.069	0.078	
HE	6.70	7.00	7.30	0.264	0.276	0.287	
θ	0°	_	10°	0°	_	10°	

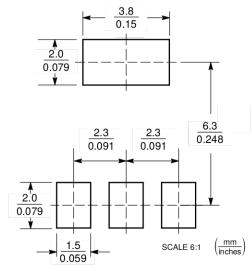
STYLE 1: PIN 1. BASE

2. COLLECTOR

3. EMITTER

4. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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